SUD45P03-15

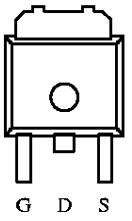
P-Channel Enhancement-Mode Transistor

Product Summary

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a]
–30	0.015 @ V_{GS} = –10 V	± 13
	0.024 @ V_{GS} = –4.5 V	± 8

TrenchFET™ Power MOSFETs

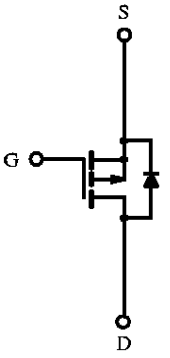
TO-252



Top View

Drain Connected to Tab

Order Number:
SUD45P03-15



P-Channel MOSFET

Absolute Maximum Ratings (T_A = 25 °C Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	–30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current[b]	T_A = 25°C	I_D	± 13	A
	T_A = 100°C		± 8	
Pulsed Drain Current		I_{DM}	± 100	
Continuous Source Current (Diode Conduction)		I_S	–13	
Maximum Power Dissipation[b]	T_C = 25°C	P_D	70	W
	T_A = 25°C		4[b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150	°C

Thermal Resistance Ratings

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b]	R_{thJA}		30	°C/W
Maximum Junction-to-Case	R_{thJC}		1.8	

Notes

a. Calculated Rating for T_A = 25° C, for comparison purposes only. This cannot be used as continuous rating (see Absolute Maximum Ratings and Typical Characteristics).

b. Surface Mounted on FR4 Board, t ≤ 10 sec.

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70267.

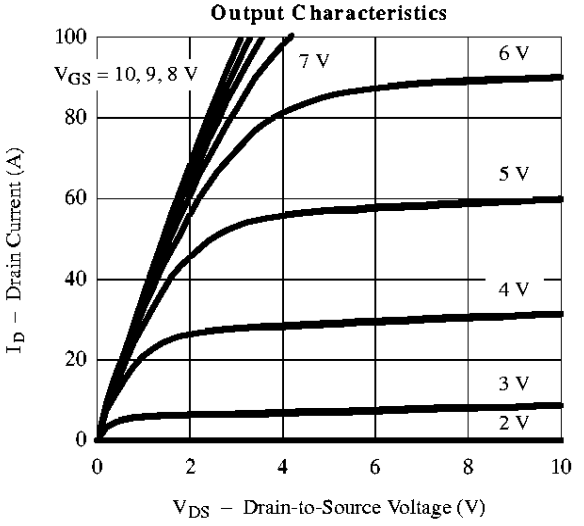
Specifications (T_J = 25°C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Min	Typ NO TAG	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = –250 µA	–30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = –250 µA	–1.0			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –30 V, V_{GS} = 0 V			–1	µA
		V_{DS} = –30 V, V_{GS} = 0 V, T_J = 125°C			–50	
On-State Drain Current[NO TAG]	$I_{D(on)}$	V_{DS} = –5 V, V_{GS} = –10 V	–50			A
		V_{DS} = –5 V, V_{GS} = –4.5 V	–20			
Drain-Source On-State Resistance[NO TAG]	$r_{DS(on)}$	V_{GS} = –10 V, I_D = –13 A		0.012	0.015	Ω
		V_{GS} = –10 V, I_D = –13 A, T_J = 125°C		0.018	0.026	
		V_{GS} = –4.5 V, I_D = –13 A		0.020	0.024	
Forward Transconductance[NO TAG]	g_{fs}	V_{DS} = –15 V, I_D = –13 A	20			S
Dynamic[NO TAG]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = –25 V, F = 1 MHz		3200		pF
Output Capacitance	C_{oss}			800		
Reverse Transfer Capacitance	C_{rss}			280		
Total Gate Charge[c]	Q_g	V_{DS} = –15 V, V_{GS} = –10 V, I_D = –45 A		50	125	nC
Gate-Source Charge[c]	Q_{gs}			14		
Gate-Drain Charge[c]	Q_{gd}			6.2		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = –15 V, R_L = 0.33 Ω I_D ≅ –45 A, V_{GEN} = –10 V, R_G = 2.4 Ω		13	20	ns
Rise Time[c]	t_r			10	20	
Turn-Off Delay Time[c]	$t_{d(off)}$			50	100	
Fall Time[c]	t_f			20	40	
Source-Drain Diode Ratings and Characteristic (T_C = 25°C)						
Pulsed Current	I_{SM}				100	A
Diode Forward Voltage[b]	V_{SD}	I_F = –45 A, V_{GS} = 0 V		1.0	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = –45 A, di/dt = 100 A/µs		55	100	ns

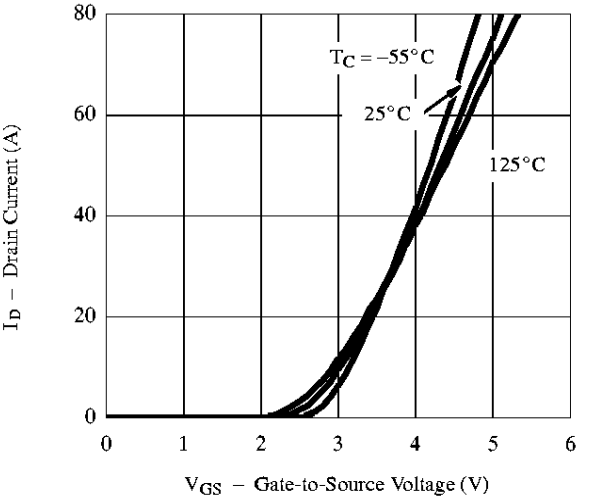
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
c. Independent of operating temperature.

Typical Characteristics (25 °C Unless Otherwise Noted)

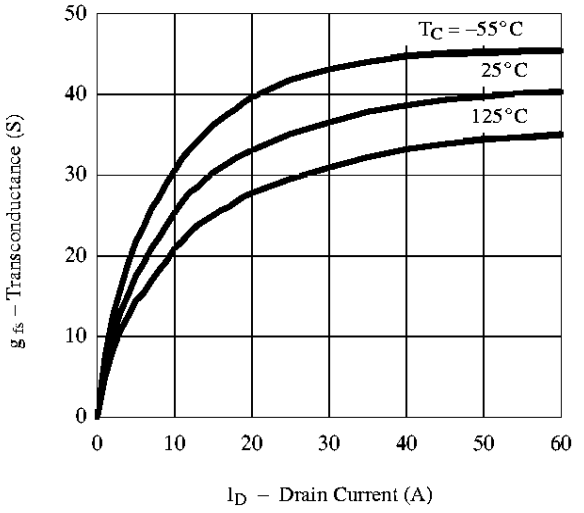
Output Characteristics



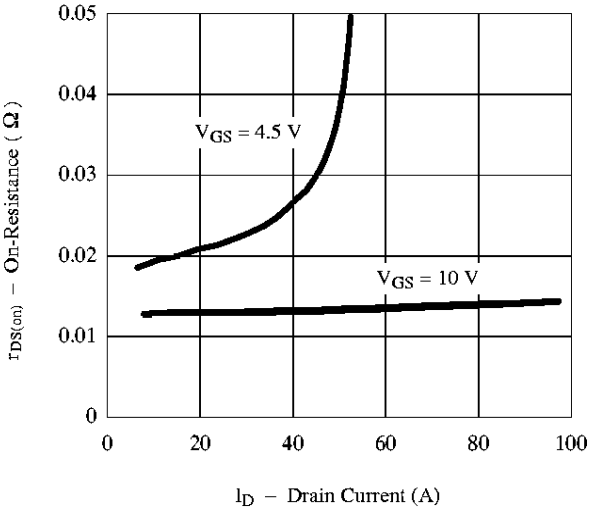
Transfer Characteristics



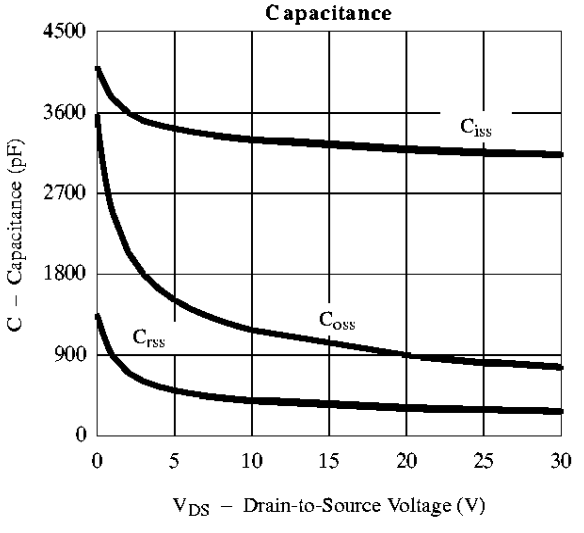
Transconductance



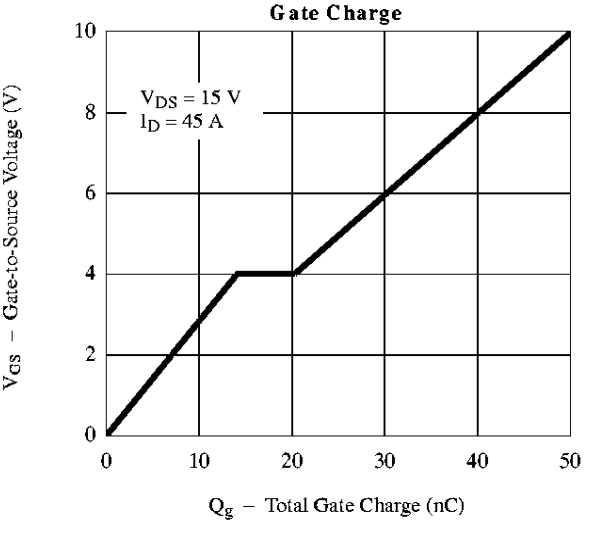
On-Resistance vs. Drain Current



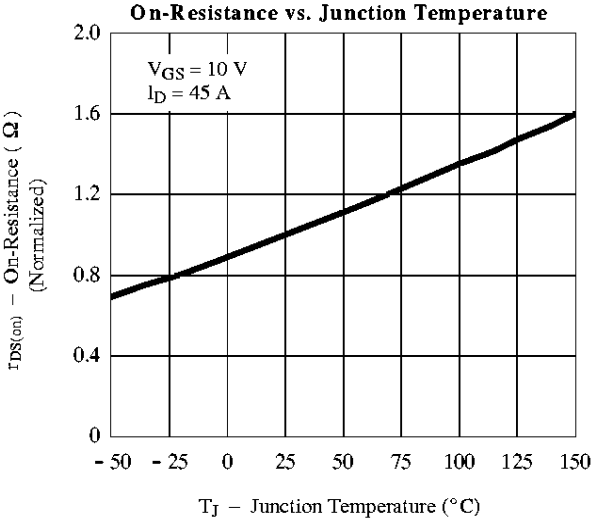
Capacitance

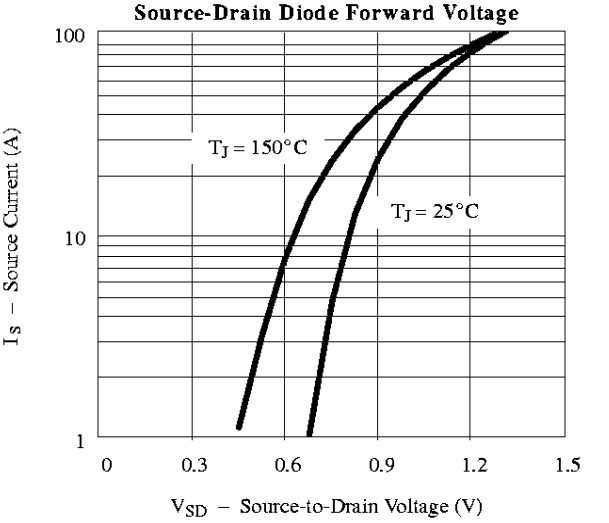
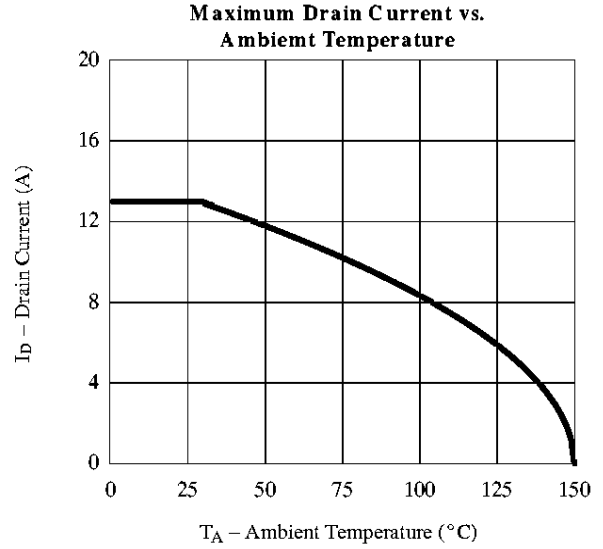
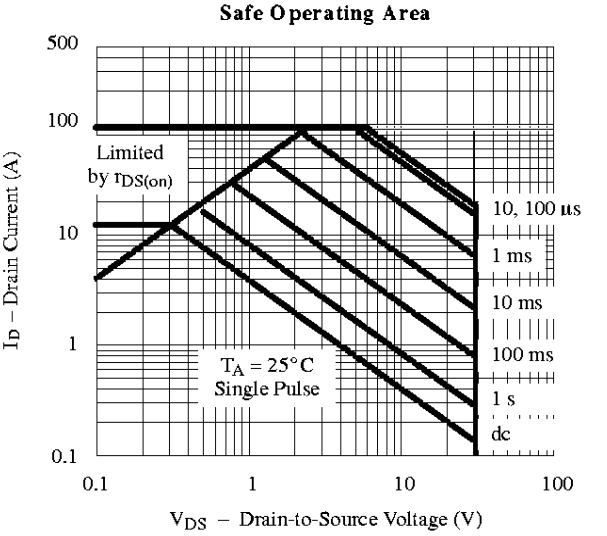
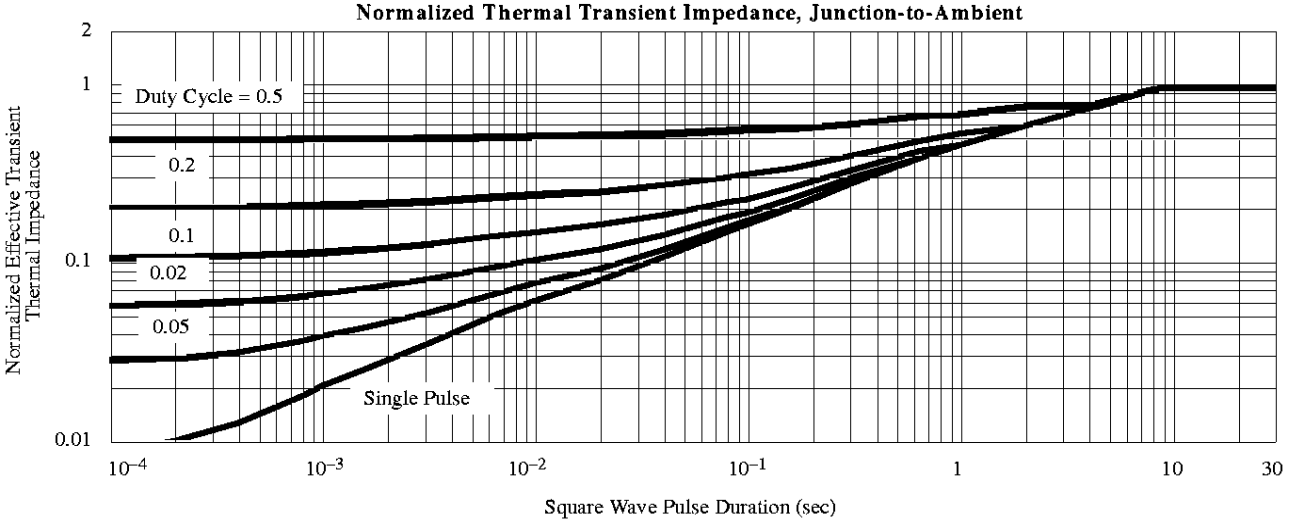


Gate Charge



Typical Characteristics (25 °C Unless Otherwise Noted)





Thermal Ratings